MOSFETs Silicon N-Channel MOS (DTMOSIV)

# TK6Q65W

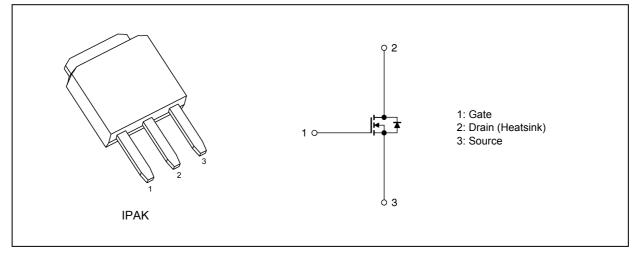
#### 1. Applications

Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.89 \Omega(typ.)$ by using Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode:  $V_{th}$  = 2.5 to 3.5 V( $V_{DS}$  = 10 V,  $I_D$  = 0.18 mA)

### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	650	V
Gate-source voltage		V <sub>GSS</sub>	±30	
Drain current (DC)	(Note 1)	I <sub>D</sub>	5.8	Α
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	23.2	1
Power dissipation (7	Г <sub>с</sub> = 25 °С)	PD	60	W
Single-pulse avalanche energy	(Note 2)	E <sub>AS</sub>	82	mJ
Avalanche current		I <sub>AR</sub>	1.5	Α
Reverse drain current (DC)	(Note 1)	I <sub>DR</sub>	5.8	1
Reverse drain current (pulsed)	(Note 1)	I <sub>DRP</sub>	23.2	7
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production 2014-09

#### 5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance		2.09	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	125	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V<sub>DD</sub> = 90 V, T<sub>ch</sub> = 25 °C (initial), L = 65.2 mH, R<sub>G</sub> = 25  $\Omega$ , I<sub>AR</sub> = 1.5 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

#### 6. Electrical Characteristics

# 6.1. Static Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±30 V, $V_{DS}$ = 0 V	_	_	±1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	650	_	—	V
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.18 mA	2.5	_	3.5	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.9 A	_	0.89	1.05	Ω

### 6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 300 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	390	—	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	1.7	—	
Output capacitance	C <sub>oss</sub>		_	12	_	
Effective output capacitance	C <sub>o(er)</sub>	$V_{DS}$ = 0 to 400 V, $V_{GS}$ = 0 V	_	17.5	_	
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN , f = 1 MHz	_	7.5	_	Ω
Switching time (rise time)	tr	See Figure 6.2.1	_	14	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	34	_	
Switching time (fall time)	t <sub>f</sub>		_	4	_	
Switching time (turn-off time)	t <sub>off</sub>	]		45	_	
MOSFET dv/dt ruggedness	dv/dt	V <sub>DD</sub> = 0 to 400 V, I <sub>D</sub> = 2.9 A	50	_	_	V/ns

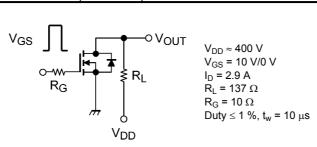


Fig. 6.2.1 Switching Time Test Circuit

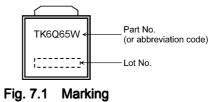
## 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS}$ = 10 V, I <sub>D</sub> = 5.8 A		11	_	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	3	_	
Gate-drain charge	Q <sub>gd</sub>			5	_	

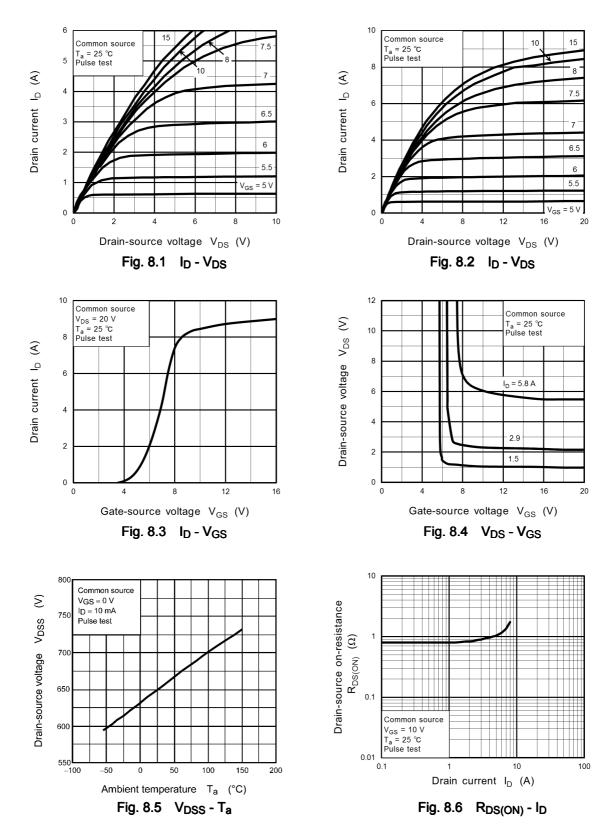
# 6.4. Source-Drain Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 5.8 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 2.9 A, V <sub>GS</sub> = 0 V	_	260	_	ns
Reverse recovery charge	Q <sub>rr</sub>	-dl <sub>DR</sub> /dt = 100 A/μs	_	1.6	_	μC
Peak reverse recovery current	I <sub>rr</sub>		_	13	_	А
Diode dv/dt ruggedness	dv/dt	$I_{DR}$ = 2.9 A, $V_{GS}$ = 0 V, $V_{DD}$ = 400 V	15			V/ns

# 7. Marking



### 8. Characteristics Curves (Note)



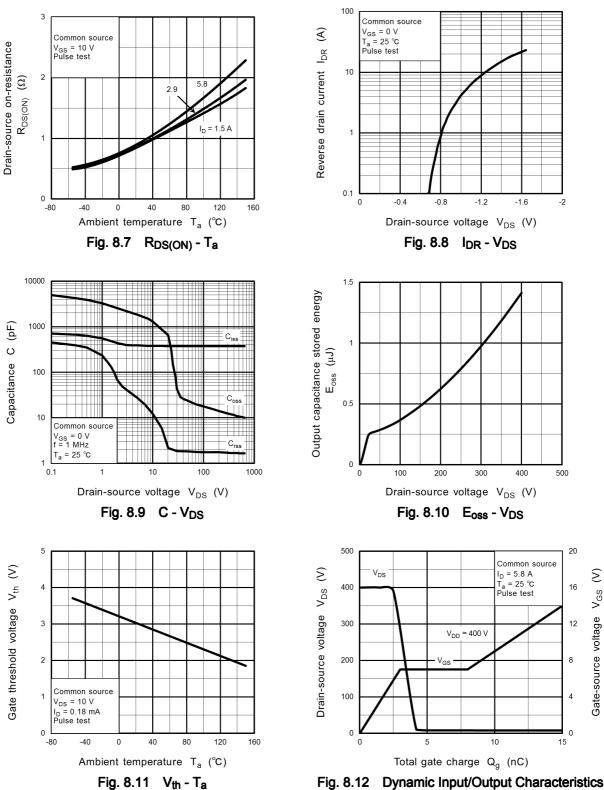
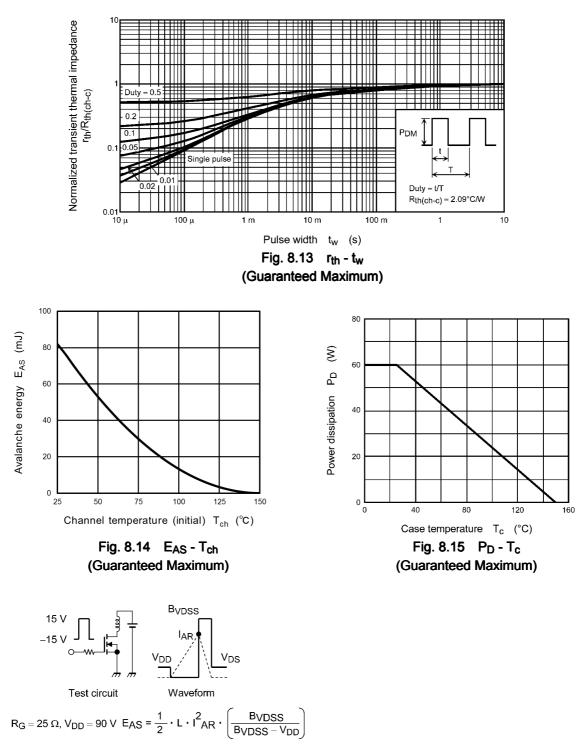
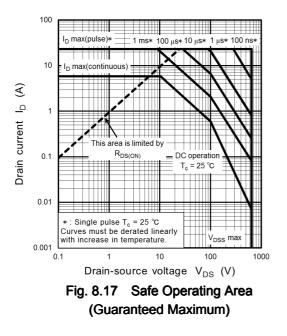


Fig. 8.12 Dynamic Input/Output Characteristics



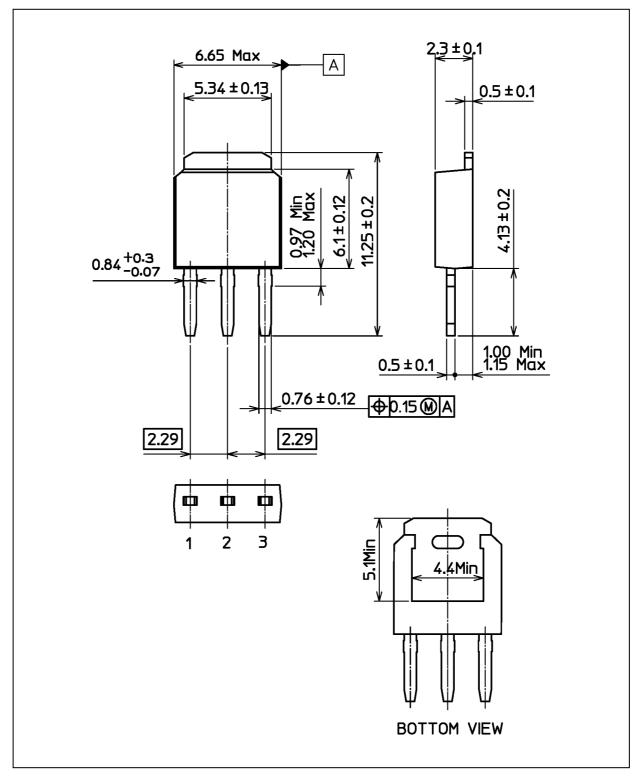




Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### **Package Dimensions**

Unit: mm



Weight: 0.337 g (typ.)

Package Name(s)

TOSHIBA: 2-7L1A

Nickname: IPAK

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